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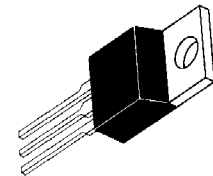
Thyristors Silicon Controlled Rectifiers

... designed for inverse parallel SCR output devices for solid state relays, welders, battery chargers, motor controls or applications requiring high surge operation.

- Photo Glass Passivated Blocking Junctions for High Temperature Stability, Center Gate for Uniform Parameters
- 550 Amperes Surge Capability
- Blocking Voltage to 800 Volts

**MCR265-2
 thru
 MCR265-10**

**SCRs
 55 AMPERES RMS
 50 thru 800 VOLTS**



**(TO-220AB)
 STYLE 3**

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted.)

Rating	Symbol	Value	Unit
Peak Repetitive Forward and Reverse Blocking Voltage ⁽¹⁾ ($T_J = 25$ to 125°C , Gate Open)	V_{DRM} V_{RRM}		Volts
MCR265-2		50	
MCR265-4		200	
MCR265-6		400	
MCR265-8		600	
MCR265-10		800	
Forward Current ($T_C = 70^\circ\text{C}$) (All Conduction Angles)	$I_T(\text{RMS})$ $I_T(\text{AV})$	55 35	Amps
Peak Non-repetitive Surge Current — 8.3 ms (1/2 Cycle, Sine Wave)	I_{TSM}	550	Amps
Forward Peak Gate Power	P_{GM}	20	Watts
Forward Average Gate Power	$P_{G(\text{AV})}$	0.5	Watt
Forward Peak Gate Current (300 μs , 120 PPS)	I_{GM}	2	Amps
Operating Junction Temperature Range	T_J	-40 to +125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-40 to +150	$^\circ\text{C}$

1. V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

These devices are rated for use in applications subject to high surge conditions. Care must be taken to insure proper heat sinking when the device is to be used at high sustained currents.



MCR265-2 thru MCR265-10

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.9	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	60	$^{\circ}\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
Peak Forward or Reverse Blocking Current ($V_{AK} = \text{Rated } V_{DRM} \text{ or } V_{RRM}, \text{ Gate Open}$) $T_J = 25^{\circ}\text{C}$ $T_J = 125^{\circ}\text{C}$	I_{DRM}, I_{RRM}	— —	— —	10 2	μA mA
Forward "On" Voltage(1) ($I_{TM} = 110 \text{ A}$)	V_{TM}	—	1.5	1.9	Volts
Gate Trigger Current (Continuous dc) (Anode Voltage = 12 Vdc, $R_L = 100 \text{ Ohms}$) ($T_C = -40^{\circ}\text{C}$)	I_{GT}	— —	20 40	50 90	mA
Gate Trigger Voltage (Continuous dc) (Anode Voltage = 12 Vdc, $R_L = 100 \text{ Ohms}$)	V_{GT}	—	1	1.5	Volts
Gate Non-Trigger Voltage (Anode Voltage = Rated V_{DRM} , $R_L = 100 \text{ Ohms}$, $T_J = 125^{\circ}\text{C}$)	V_{GD}	0.2	—	—	Volts
Holding Current (Anode Voltage = 12 Vdc, Gate Open)	I_H	—	30	75	mA
Turn-On Time ($I_{TM} = 55 \text{ A}$, $I_{GT} = 200 \text{ mAdc}$)	t_{gt}	—	1.5	—	μs
Critical Rate-of-Rise of Off-State Voltage (Gate Open, $V_D = \text{Rated } V_{DRM}$, Exponential Waveform)	dv/dt	—	50	—	$\text{V}/\mu\text{s}$

1. Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2\%$.

FIGURE 1 — AVERAGE CURRENT DERATING

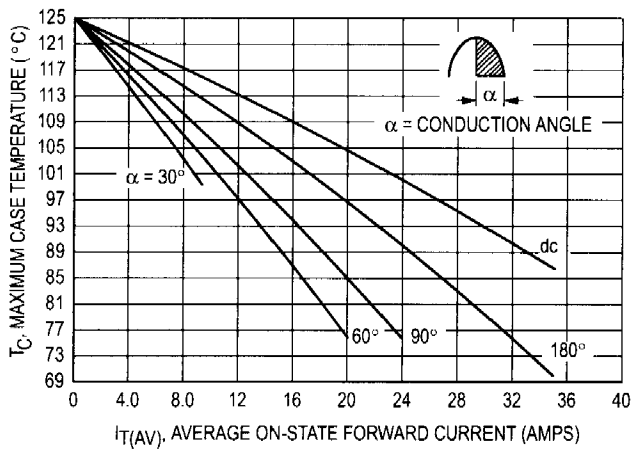


FIGURE 2 — MAXIMUM ON-STATE POWER DISSIPATION

